SCS215AE

SiC Schottky Barrier Diode

Datasheet

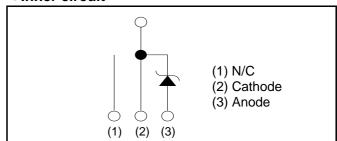
V_R	650V
I _F	15A
Q_{C}	23nC

● Outline TO-247 (1) (2) (3)

Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible

•Inner circuit



Applications

- PFC Boost Topology
- Secondary Side Rectification
- Data Center
- PV Power Conditioners

●Packaging specifications

	aging opcomoduono	
	Packaging	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCS215AE

•Absolute maximum ratings $(T_i = 25^{\circ}C)$

Parameter		Symbol Value		Unit	
Reverse voltage (repetitive peak)		V _{RM} 650		V	
Reverse voltage (De	C)	V_R	650	V	
Continuous forward	current (T _c = 134°C)	I _F	I _F 15/30		
Surge non-	PW=10ms sinusoidal, T _j =25°C		52	А	
repetitive forward	PW=10ms sinusoidal, T _j =150°C I _{FSM}		41	А	
current	PW=10μs square, T _j =25°C		200	А	
Repetitive peak forward current		I _{FRM}	65 *1	А	
PW=10ms, T _j =25°C		$\int i^2 dt$	13	A ² s	
i ² t value PW=10ms, T _j =150°C		J i⁻dt	8.4	A ² s	
Total power disspation		P_{D}	110 *2	W	
Junction temperature		T _j	175	°C	
Range of storage temperature		T _{stg}	-55 to +175	°C	

^{*1} T_c=100°C, T_i=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics (T_j = 25°C)

Parameter Sym	Symbol	Symbol Conditions -	Values			Linit
	Symbol		Min.	Тур.	Max.	Unit
DC blocking voltage	V_{DC}	I _R =3.0mA	650	-	-	V
	V _F	I _F =15A,T _j =25°C	-	1.35	1.55	V
Forward voltage		I _F =15A,T _j =150°C	-	1.55	-	V
		I _F =15A,T _j =175°C	-	1.63	-	V
Reverse current	I _R	V _R =600V,T _j =25°C	-	3	300	μΑ
		V _R =600V,T _j =150°C	-	45	-	μΑ
		V _R =600V,T _j =175°C	-	105	-	μΑ
Total capacitance	С	V _R =1V,f=1MHz	-	550	-	pF
		V _R =600V,f=1MHz	-	56	-	pF
Total capacitive charge	Q _C	V _R =400V,di/dt=350A/μs	-	23	-	nC
Switching time	t _C	V _R =400V,di/dt=350A/μs	-	18	-	ns

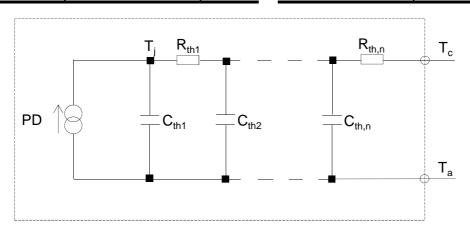
Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Thermal resistance	R _{th(j-c)}	-	-	1.1	1.3	°C/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	2.90E-01	
R _{th2}	8.03E-01	K/W
R _{th3}	8.54E-03	

Symbol	Value	Unit
C _{th1}	2.33E-03	
C _{th2}	8.15E-03	Ws/K
C _{th3}	5.82E-01	



•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics

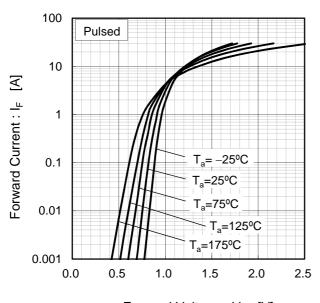
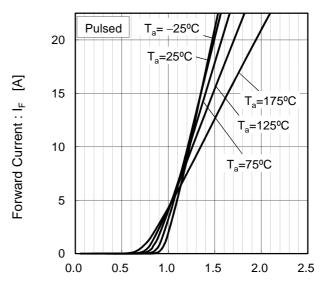


Fig.2 V_F - I_F Characteristics



Forward Voltage : V_F [V]

Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics

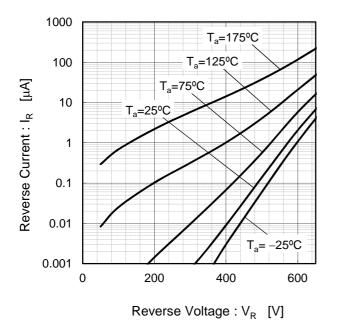
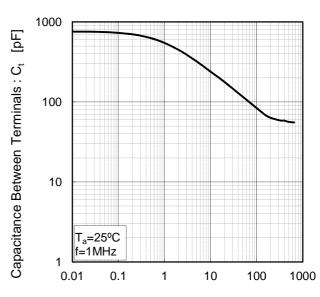
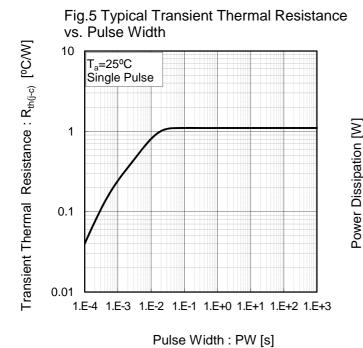


Fig.4 V_R - C_t Characteristics



Reverse Voltage : V_R [V]

•Electrical characteristic curves



140 120 100 80 60 40 20 0 25 50 75 100 125 150 175

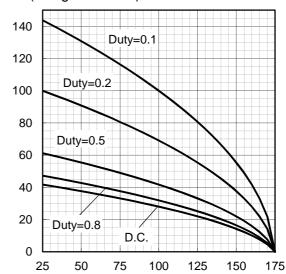
Fig.6 Power Dissipation

Fig.7*3 Maximum peak forward current derating curve I_P - T_c 140 120 Peak Forward Current : Ip [A] Duty=0.1 100 Duty=0.2 80 60 Duty=0.5 40 20 Duty=0.8 D.C. 0 25 50 75 100 125 150 175

Case Temperature : T_c [°C] *3 Based on max Vf, max $R_{th(j-c)}$ Valid for switching of above 10kHz, excluding D.C. curve.

Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed)

Case Temperature : T_c [°C]

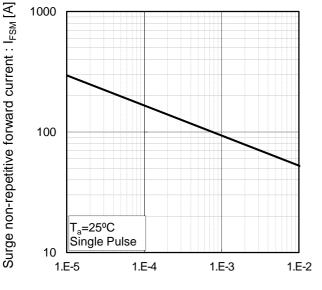


Case Temperature : T_c [°C] *4 Based on typ Vf, typ R_{th(j-c)} Typical value, not guaranteed Valid for switching of above 10kHz, excluding D.C. curve

Peak Forward Current : IP [A]

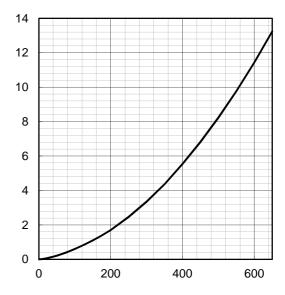
Electrical characteristic curves

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)



Pulse Width: PW [s]

Fig.10 Typical capacitance store energy

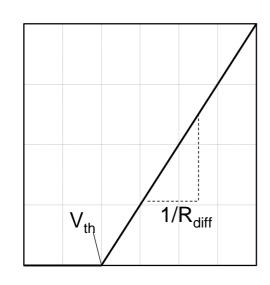


Capacitance stored energy : $\mathsf{E}_{_{\mathrm{C}}}[\mu \mathsf{J}]$

Reverse Voltage: V_R [V]

Symplified forward characteristic model

Fig.11 Equivalent forward current curve



Forward Voltage: V_F

$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th} (T_j) = a_0 + a_1 T_j$$

 $R_{diff} (T_j) = b_0 + b_1 T_j + b_2 T_j^2$

Symbol	Typical Value	Unit
a ₀	9.35E-01	V
a ₁	-1.12E-03	V/°C
b ₀	2.65E-02	Ω
b ₁	6.80E-05	Ω/°C
b ₂	7.20E-07	$\Omega/^{\circ}C^{2}$

 T_i in °C; -55 °C < T_i < °C; I_F < 30 A

Forward Current: IF

Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications:
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products specified in this document are not designed to be radiation tolerant.
- 7) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, and power transmission systems.
- 8) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 9) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 10) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 11) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 12) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 13) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor: SCS215AEC